



US 20240179910A1

(19) **United States**(12) **Patent Application Publication****Kim et al.**(10) **Pub. No.: US 2024/0179910 A1**(43) **Pub. Date: May 30, 2024**

(54) **SEMICONDUCTOR MEMORY DEVICE,  
METHOD FOR FABRICATING THE SAME  
AND ELECTRONIC SYSTEM INCLUDING  
THE SAME**

*H01L 25/065* (2006.01)*H01L 25/18* (2006.01)*H10B 80/00* (2006.01)(52) **U.S. Cl.**

CPC ..... *H10B 43/27* (2023.02); *H01L 24/08*  
(2013.01); *H01L 25/0657* (2013.01); *H01L*  
*25/18* (2013.01); *H10B 80/00* (2023.02); *H01L*  
*2224/08145* (2013.01); *H01L 2924/1431*  
(2013.01); *H01L 2924/14511* (2013.01)

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(21) Appl. No.: **18/355,718**

(22) Filed: **Jul. 20, 2023**

(30) **Foreign Application Priority Data**

Nov. 24, 2022 (KR) ..... 10-2022-0159141

**Publication Classification**

(51) **Int. Cl.**

*H10B 43/27* (2006.01)*H01L 23/00* (2006.01)(57) **ABSTRACT**

A semiconductor memory device includes a cell substrate including a first surface and a second surface opposite to the first surface, a first mold stack including a plurality of first gate electrodes sequentially stacked on the first surface, a second mold stack including a plurality of second gate electrodes sequentially stacked on the first mold stack, a first channel structure extending in a first direction with respect to the first surface and crossing the plurality of first gate electrodes and the plurality of second gate electrodes, and an input/output pad on the second surface, wherein the first mold stack includes a mold opening that exposes a portion of the second mold stack, and at least a portion of the input/output pad overlaps the mold opening in the first direction.

